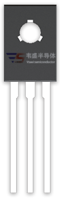
KSB1151 TRANSISTOR (PNP)

FEATURES

- Low Collector-Emitter Saturation Voltage
- Large Collector Current
- High Power Dissipation
- Complement to KSD1691


TO-126

1.EMITTER
2.COLLECTOR
3.BASE

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
KSB1151	TO-126	Bulk	200pcs/Bag
KSB1151-TU	TO-126	Tube	60pcs/Tube

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

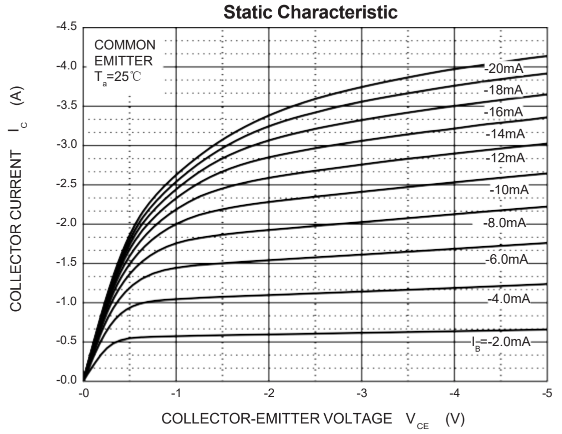
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current	-5	A
P_C	Collector Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	100	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

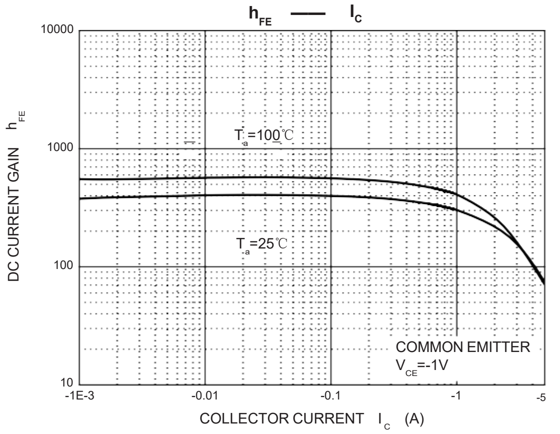
T_a=25℃ unless otherwise specified

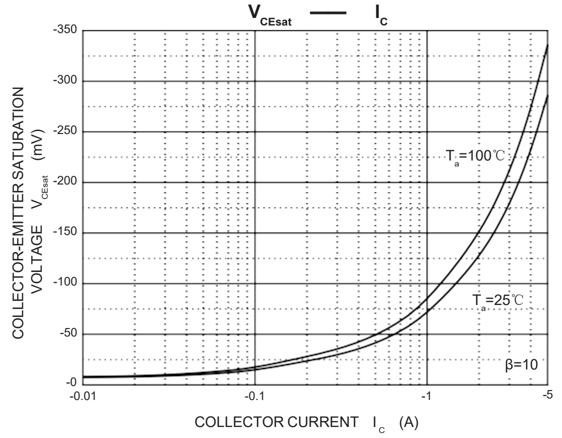
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	-7			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0			-10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-7V,I_C=0			-10	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-2A	100		400	
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-0.1A	60			
	$h_{FE(3)}$	V_{CE}=-2V, I_C=-5A	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-2A,I_B=-0.2A			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-2A,I_B=-0.2A			-1.2	V

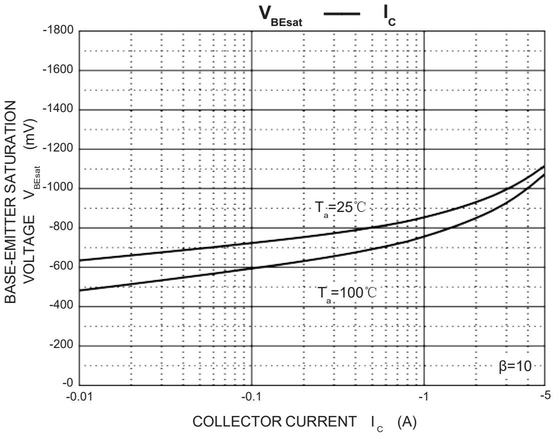
CLASSIFICATION OF $h_{FE(1)}$

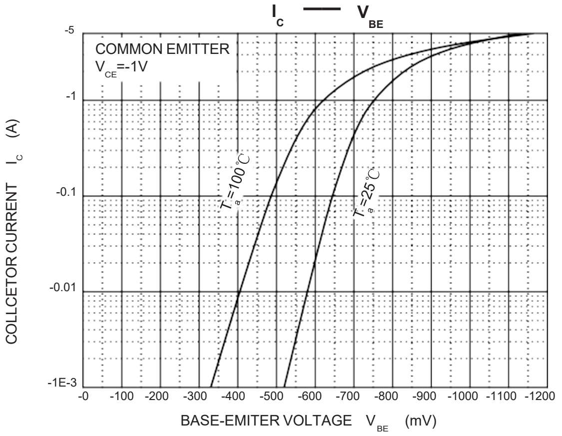
RANK	O	Y	G
RANGE	100-200	160-320	200-400

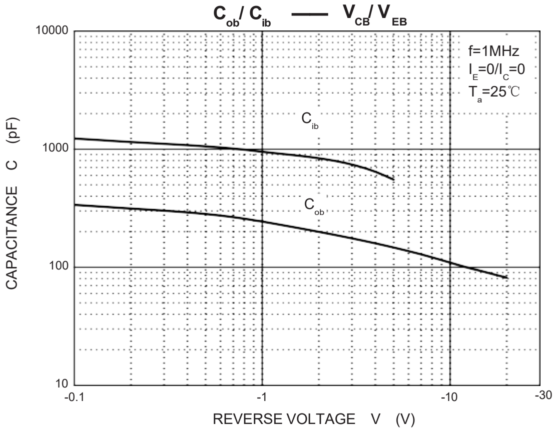

Static Characteristic

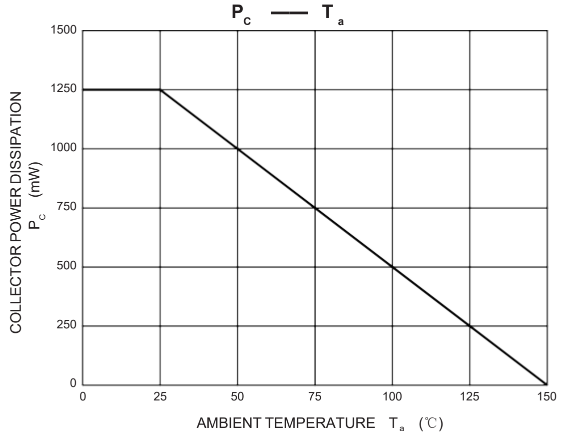

h_{FE} — I_C


V_{CEsat} — I_C


V_{BEsat} — I_C


I_C — V_{BE}


C_{ob}/ C_{ib} — V_{CB}/ V_{EB}


P_C — T_a